# Zhigang Jia

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/9442942/publications.pdf

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|---|---|---|---|
| 12 papers | 150 citations | 1306789 7 h-index | 1199166 12 g-index |
| 12 all docs | 12 docs citations | 12 times ranked | 260 citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | The evolution of a GaN/sapphire interface with different nucleation layer thickness during two-step growth and its influence on the bulk GaN crystal quality. RSC Advances, 2015, 5, 51201-51207. | 1.7 | 23 |
| 2 | Understanding the Growth Mechanism of GaN Epitaxial Layers on Mechanically Exfoliated Graphite. Nanoscale Research Letters, 2018, 13, 130. | 3.1 | 21 |
| 3 | Effect of hydrogen treatment temperature on the properties of InGaN/GaN multiple quantum wells. Nanoscale Research Letters, 2017, 12, 321. | 3.1 | 20 |
| 4 | Enhancement of carrier localization effect and internal quantum efficiency through In-rich InGaN quantum dots. Superlattices and Microstructures, 2018, 113, 497-501. | 1.4 | 19 |
| 5 | GaN epitaxial layers grown on multilayer graphene by MOCVD. AIP Advances, 2018, 8, . | 0.6 | 18 |
| 6 | Effect of potential barrier height on the carrier transport in InGaAs/GaAsP multi-quantum wells and photoelectric properties of laser diode. Physical Chemistry Chemical Physics, 2016, 18, 6901-6912. | 1.3 | 15 |
| 7 | Surface Morphology Evolution Mechanisms of InGaN/GaN Multiple Quantum Wells with Mixture N2/H2-Grown GaN Barrier. Nanoscale Research Letters, 2017, 12, 354. | 3.1 | 13 |
| 8 | Small-size graphene oxide (GO) as a hole injection layer for high-performance green phosphorescent organic light-emitting diodes. Journal of Materials Chemistry C, 2021, 9, 12408-12419. | 2.7 | 7 |
| 9 | Growth and optical properties of GaN pyramids using in-situ deposited SiNx layer. Materials Letters, 2018, 224, 86-88. | 1.3 | 5 |
| 10 | The formation of island-shaped morphology on the surface of InGaN/GaN QWs and the enhancement of carrier localization effect caused by high-density V-shaped pits. Materials Science in Semiconductor Processing, 2021, 131, 105848. | 1.9 | 4 |
| 11 | The morphologies and optical properties of three-dimensional GaN nano-cone arrays. RSC Advances, 2016, 6, 43272-43277. | 1.7 | 3 |
| 12 | Improving the internal quantum efficiency of QD/QW hybrid structures by increasing the GaN barrier thickness. RSC Advances, 2020, 10, 41443-41452. | 1.7 | 2 |